

Name: \_\_\_\_\_

Student ID #: \_\_\_\_\_

EECS 170A  
Homework #2

HW will be collected in DISCUSSION, TA OFFICE HOURS, OR A SPECIAL TURN-IN SECTION ON  
FRIDAY OCT 15 FROM 12-12:30 pm.

(Location of special turn-in section to be announced.)

Do not turn your HW in anywhere else, or it will not be accepted.

You are encouraged to turn it in at your own discussion section.

You may turn it in at any discussion section.

Last option to turn in: Special turn-in session, October 15, 2004, 12-12:30.

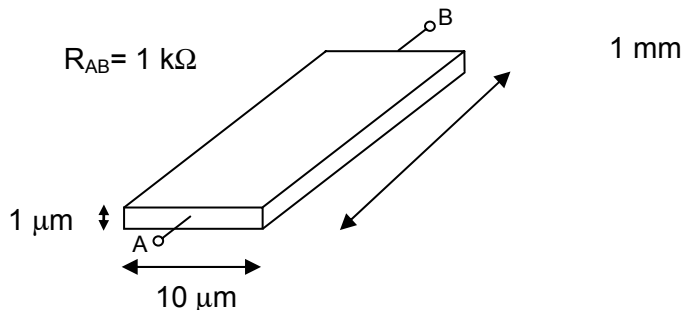
DUE: 12:30 PM Friday, October 15, 2004.

Please *staple* this sheet to the front of your homework.

1a	1b	2a	2b	2c	2d	3a	3b	Total
/10	/10	/15	/15	/15	/15	/10	/10	/100

- 1) A thin metal film resistor as shown in the figure below has a resistance of 1 MΩ. It is 1 mm long, 10 μm wide, and 1 μm thick.

- Calculate the resistivity ( $\rho$ ), in units of Ω-m.
- Now express the resistivity in units of μΩ-cm, a more common unit.



- 2) For Si at 300 K, do the following: (Use  $\text{cm}^{-3}$  as your units.)

- $N_D = 10^{20} \text{ cm}^{-3}$ ;  $N_A \ll N_D$ . Calculate the equilibrium electron concentration ( $n$ ) and hole concentration ( $p$ ).
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- $N_A = 10^{20} \text{ cm}^{-3}$ ;  $N_D \ll N_A$ . Calculate the equilibrium electron concentration ( $n$ ) and hole concentration ( $p$ ).
- $N_A = 10^{10} \text{ cm}^{-3}$ ;  $N_D \ll N_A$ . Calculate the equilibrium electron concentration ( $n$ ) and hole concentration ( $p$ ).

- 3) For the silicon sample at  $T = 300 \text{ K}$  shown below, given  $N_A = 10^{17} \text{ cm}^{-3}$ ,  $N_D \ll N_A$ ,

- Find the resistivity  $\rho$  of the Si to within 10%. For units, use Ω-cm. (You may use figure 3.8 from the text.)
- Calculate the resistance  $R_{AB}$  in units of Ω, for the following geometry:

